

HZM6.8ZMFA

Silicon Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-783A(Z)

Rev 1

Nov. 1999

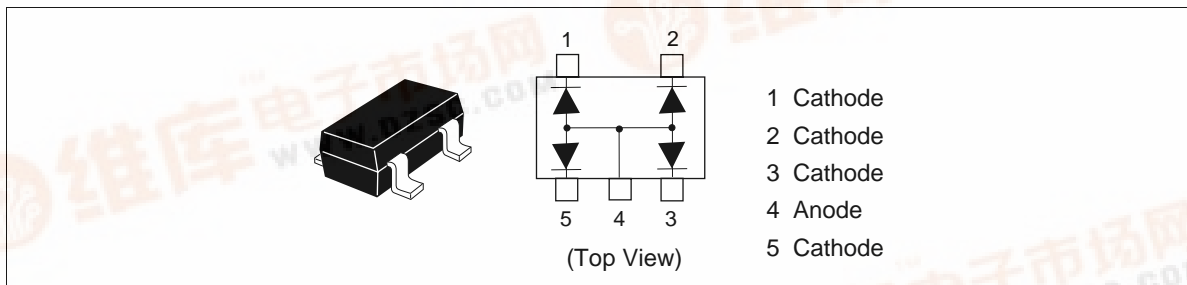
Features

- HZM6.8ZMFA has four devices in a monolithic, and can absorb surge.
- Low capacitance ($C=25\text{pF}$ max) and can protect ESD of signal line.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.8ZMFA	68N	MPAK-5

Outline



HZM6.8ZMFA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd ^{*1}	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, See Fig.2.

Electrical Characteristics (Ta = 25°C) ^{*1}

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _Z	6.47	—	7.00	V	I _Z = 5 mA, 40ms pulse
Reverse current	I _R	—	—	2	μA	V _R = 3.5V
Capacitance	C	—	—	25	pF	V _R = 0V, f = 1 MHz
Dynamic resistance	r _d	—	—	30	Ω	I _Z = 5 mA
ESD-Capability ^{*2 *3}	—	25	—	—	kV	C = 150pF, R = 330Ω, Both forward and reverse direction 10 pulse

- Notes
1. Per one device.
 2. Failure criterion ; I_R > 2 μA at V_R = 3.5V.
 3. Between cathode and anode.

Main Characteristic

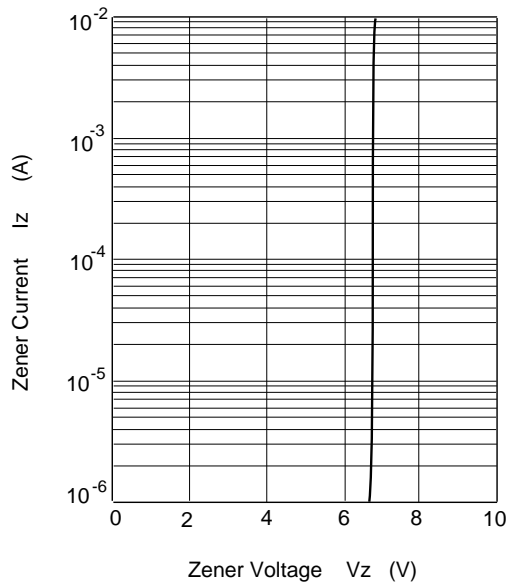


Fig.1 Zener current Vs. Zener voltage

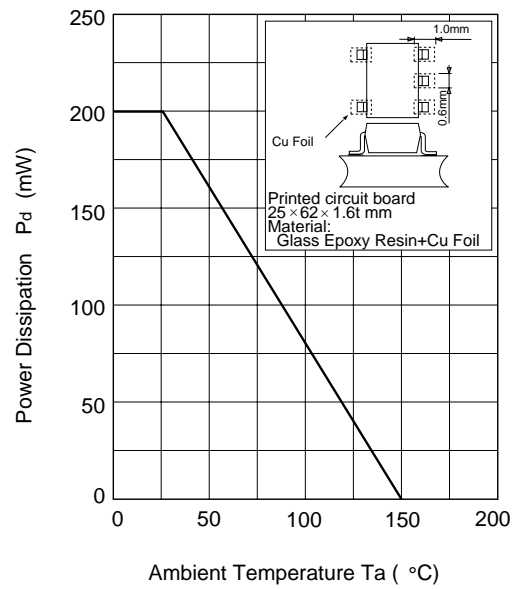


Fig.2 Power Dissipation Vs. Ambient Temperature

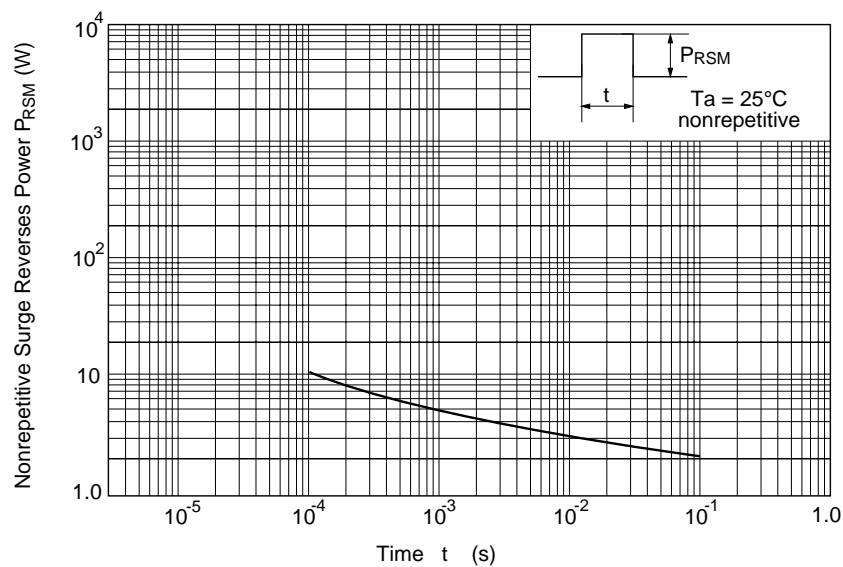
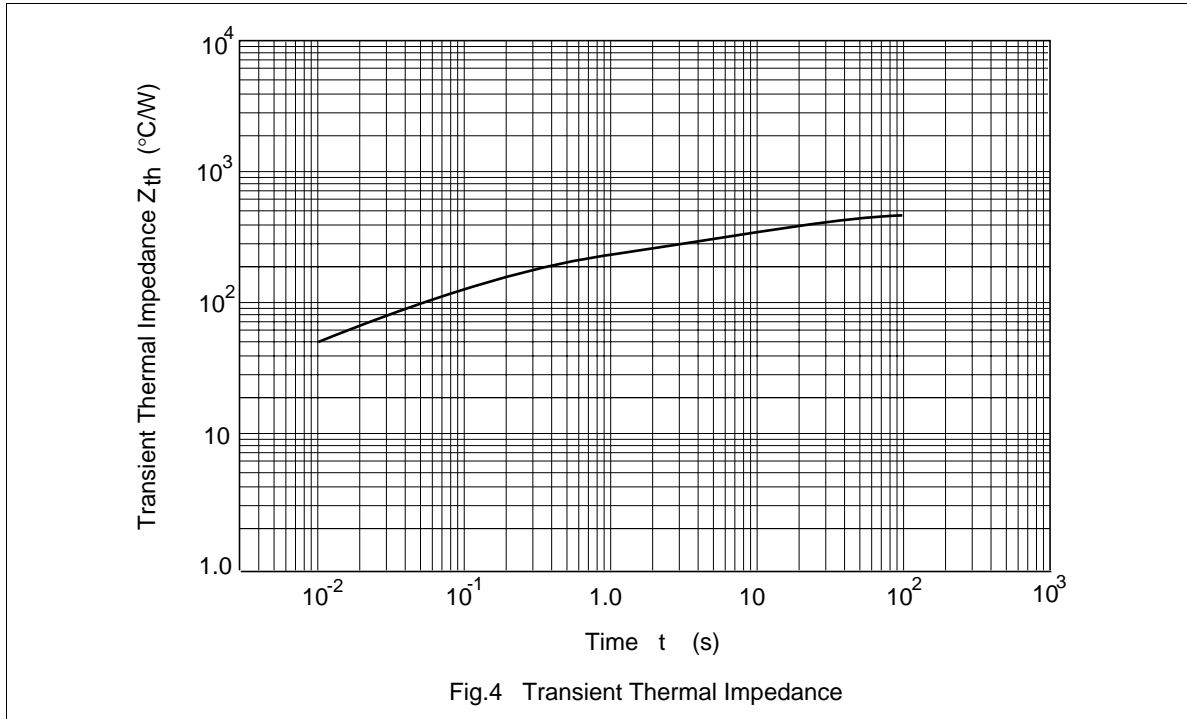


Fig.3 Surge Reverse Power Ratings

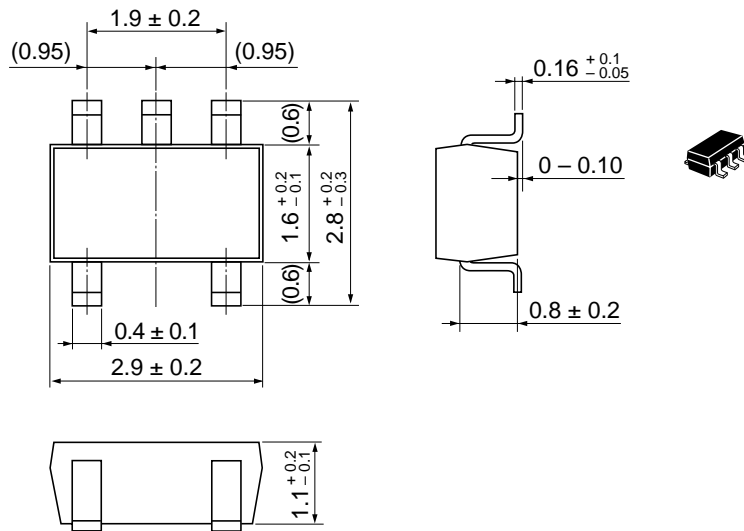
HZM6.8ZMFA

Main Characteristic



Package Dimensions

Unit: mm



Hitachi Code	MPAK-5
JEDEC	—
EIAJ	—
Mass	0.013 g

HZM6.8ZMFA

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